

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Atty. Docket

DOEDE TERPSTRA ET AL

NL 000383

Serial No.

Group Art Unit

Filed: CONCURRENTLY

Ex.

Title: METHOD OF MANUFACTURING A BIPOLAR TRANSISTOR SEMICONDUCTOR  
DEVICE

Commissioner for Patents  
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination, please  
amend the above-identified application as follows:

IN THE CLAIMS

Please amend the claims as follows:

91  
3. (amended) A method as claimed in claim 1, characterized in  
that after the formation of the intrinsic base region, a layer of  
an electrically insulating material is provided, which is subjected  
to an etching operation so as to form spacers on edges of the base  
contact and the collector contact, causing these contacts to be